

**Amendments to the Claims:**

Please amend Claim 1 and add Claims 43 – 58 as indicated in the following listing of claims, which replaces all prior versions and listings of claims in the application.

**Listing of Claims:**

1. (Currently Amended) A method for ~~preventing dopant leaching from a doped structural film during fabrication of~~ fabricating a microelectromechanical system, the method comprising:

producing an intermediate microstructure that includes ~~the~~ a doped structural film, sacrificial material, and metallic material ~~by a combination of techniques selected from the group consisting of deposition, patterning, and etching;~~

dissolving the sacrificial material from the intermediate microstructure with an acid to form the microelectromechanical system ~~release solution, the release solution comprising a substance destructive to the sacrificial material and acting as an electrolyte to form a galvanic cell with the doped structural film and metallic material acting as electrodes;~~ and

suppressing ~~effects of the galvanic cell~~ dopant leaching from the doped structural film while dissolving the sacrificial material by including a nonionic detergent ~~mixed~~ in the ~~release solution~~ acid.

2. – 42. (Canceled)

43. (New) The method recited in claim 1 wherein the doped structural film comprises a doped semiconductor.

44. (New) The method recited in claim 1 wherein the doped structural film comprises doped silicon.

45. (New) The method recited in claim 44 wherein the doped structural film comprises doped polysilicon.

46. (New) The method recited in claim 1 wherein the metallic material comprises a material selected from the group consisting of gold, aluminum, copper, platinum, and nickel.

47. (New) The method recited in claim 1 wherein the nonionic detergent comprises an alkyl group and a polyether-linked hydroxy group commonly linked to an aryl group.

48. (New) The method recited in claim 1 wherein the nonionic detergent is included with a concentration relative to the acid approximately between 0.01 and 0.1 vol. %.

49. (New) The method recited in claim 1 wherein the nonionic detergent comprises a hydrophilic moiety and a hydrophobic moiety commonly linked to an aryl group.

50. (New) A microelectromechanical system fabricated according to the method recited in claim 1.

51. (New) A method for fabricating a microelectromechanical system, the method comprising:

producing an intermediate microstructure that includes a doped silicon film, sacrificial material, and a metallic material selected from the group consisting of gold, aluminum, copper, platinum, and nickel;

dissolving the sacrificial material from the intermediate microstructure with an acid to form the microelectromechanical system; and

suppressing dopant leaching from the doped silicon film while dissolving the sacrificial material by including a substance comprising an alkyl group and a polyether-linked hydroxy group commonly linked to an aryl group in the acid.

52. (New) The method recited in claim 51 wherein the doped silicon film comprises a doped polysilicon film.

53. (New) The method recited in claim 51 wherein the substance is included with a concentration relative to the acid approximately between 0.01 and 0.1 vol.%.

54. (New) A microelectromechanical system made according to the method recited in claim 51.

55. (New) A method for fabricating a microelectromechanical system, the method comprising:

producing an intermediate microstructure that includes a doped silicon film, sacrificial material, and a metallic material selected from the group consisting of gold, aluminum, copper, platinum, and nickel;

dissolving the sacrificial material from the intermediate microstructure with an acid to form the microelectromechanical system; and

suppressing dopant leaching from the doped structural film while dissolving the sacrificial material by including a substance comprising a hydrophilic moiety and a hydrophobic moiety commonly linked to an aryl group in the solution.

56. (New) The method recited in claim 55 wherein the doped silicon film comprises a doped polysilicon film.

57. (New) The method recited in claim 55 wherein the substance is included with a concentration relative to the acid approximately between 0.01 and 0.1 vol.%.

58. (New) A microelectromechanical system made according to the method recited in claim 55.